

**Notice of References Cited**

Application/Control No.

09/856,823

Applicant(s)/Patent Under  
Reexamination  
HASHIMOTO ET AL.

Examiner

Matthew J Song

Art Unit

1765

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**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	B	US-6,100,575	08-2000	Minato, Tadaharu	257/617
	C	US-4,819,037	04-1989	Sakakibara et al.	257/24
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	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
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**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Sun et al. "Suppression of Cobalt Silicide Agglomeration Using Nitrogen Implantation", IEEE Electron Device Letters, Vol 19, N 5, May 1998.
	V	Sun et al., "Impact of Nitrogen Implantation into Polysilicon Gate on Thermal Stability of Cobalt Silicide Formed on Polysilicon Gate", IEEE Transactions of Electron Devices, Vol 45, No 9, September 1998.
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.